

AMENDMENTS TO THE CLAIMS

1-44. (Cancelled)

45. (Currently Amended) A semiconductor device comprising:

an insulating layer; and

an ammonia-cleaned, etched opening in said insulating layer; and[[,]]

a conductor ~~formed~~ in said ammonia-cleaned, etched opening.

46. (Currently Amended) An integrated circuit comprising:

an ammonia-cleaned, etch residue-free High Aspect Ratio opening provided in an insulating layer, said opening being formed ~~atop~~ over a polysilicon region[[,]] : and

a conductor within said opening, ~~containing a conductor which said~~
conductor being electrically ~~connects~~ connected with said polysilicon region.

47. (Currently Amended) An integrated circuit as in claim 46 further comprising [[:]] a silicide layer between said conductor and said polysilicon region.

48. (Original) An integrated circuit as in claim 46, wherein said integrated circuit is a memory circuit.

49. (Original) An integrated circuit as in claim 47 wherein the interface area between said conductor and polysilicon region is free of oxygen contamination.

50-53. (Cancelled)